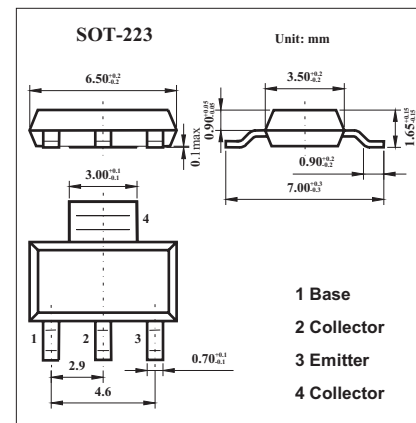


## PNP Silicon Extremely High Voltage Darlington Transistor CZT2000

### ■ Features

●



### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	200	V
Emitter-Base Voltage	V <sub>EBO</sub>	10	V
Collector Current	I <sub>C</sub>	600	mA
Power Dissipation	P <sub>D</sub>	2	W
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to 150	°C
Thermal Resistance	Θ <sub>JA</sub>	62.5	°C/W

### ■ Electrical Characteristics Ta = 25°C

Symbol	Testconditions	Min	Max	Unit
I <sub>CBO</sub>	V <sub>CB</sub> =180V		500	nA
I <sub>EBO</sub>	V <sub>BE</sub> =10V		100	nA
B <sub>VCE(S)</sub>	I <sub>C</sub> =1.0mA	200		V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =20mA, I <sub>B</sub> =25μA		0.9	V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =80mA, I <sub>B</sub> =40μA		1.1	V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =160mA, I <sub>B</sub> =100μA		1.2	V
V <sub>BE(ON)</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =160mA		2.0	V
h <sub>FE</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =100μA	3,000		
	V <sub>CE</sub> =5.0V, I <sub>C</sub> =10mA	3,000		
	V <sub>CE</sub> =5.0V, I <sub>C</sub> =160mA	3,000		